



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

PATENT

Applicant(s): Ulrike Gruening et al.

Serial No.: 09/669,585.

Filing Date: September 26, 2000

Entitled: **IMPROVED TRENCH CAPACITOR  
MEMORY CELL**

Docket No.: 00P7925US (IFX-060PUS)

Group Art Unit: 2811

Examiner: C. Nguyen

#6/a  
10/23/02  
Amirth

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By: Tanya Blount

Tanya Blount

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**AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

In response to the Office Action date mailed May 17, 2002, please amend the above-identified application as follows:

**In the Claims:**

A clean copy of the amended claims is below, a comparison copy is attached:

*Sub*  
*A, B*

(Amended) A memory cell comprising:  
a trench capacitor formed in a substrate;  
a shallow transistor trench (STT) formed in the substrate;  
a transistor comprising:

a first diffusion region, the first diffusion region couples the capacitor to a gate of the transistor;

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